



## PATENT ABSTRACTS OF JAPAN

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(21) Application number: **05044707**(22) Date of filing: **08.02.1993**(71) Applicant: **CASIO COMPUT CO LTD**(72) Inventor: **YAMADA HIROYASU**(54) **PHOTOSENSOR**

## (57) Abstract:

**PURPOSE:** To provide a photosensor, which has the photosensor function and the selecting-transistor function and has the excellent switching characteristic.

**CONSTITUTION:** A photosensor 20 has a bottom a gate electrode 22 on an insulating substrate 21 and a bottom-gate insulating film 23 covering the electrode. A semiconductor layer 24 is further formed thereon. A source electrode 25 and a drain electrode 26 are formed so as to hold the semiconductor layer 24. A top gate insulating film 29 covers these parts. A top gate electrode 30 is formed thereon. A specified interval is formed between the d edge part of the top gate electrode 30 on the side of the source electrode 2 and

the edge part on the side of the source electrode 25. The interval becomes an offset region D. Even if light is cast at the time of offset, the flow of a c drain current is prevented by the offset region D.

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